

NTE2324

Silicon NPN Transistor

Color TV Horizontal Deflection Output

Applications:

- Color TV Horizontal Deflection Output

Features:

- High Speed ($t_f = 100\text{nsec}$)
- High Breakdown Voltage ($V_{CBO} = 1500\text{V}$)
- High Reliability (adoption of HVP process)

Absolute Maximum Ratings:

Collector to Base Voltage, V_{CBO}	1500V
Collector to Emitter Voltage, V_{CEO}	800V
Emitter to Base Voltage, V_{EBO}	6V
Collector Current, I_C	
Continuous	8A
Peak	30A
Collector Dissipation ($T_C = +25^\circ\text{C}$), P_C	70W
Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	-55° to +150°C

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CES}	$V_{CE} = 1500\text{V}$	—	—	1.0	mA
	I_{CBO}	$V_{CB} = 800\text{V}$	—	—	10	μA
Collector Sustain Voltage	$V_{CEO(sus)}$	$I_C = 100\text{mA}$, $I_B = 0$	800	—	—	V
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 4\text{V}$	—	—	1.0	mA
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 6\text{A}$, $I_B = 1.2\text{A}$	—	—	5.0	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 6\text{A}$, $I_B = 1.2\text{A}$	—	—	1.5	V
DC Current Gain	h_{FE}	$V_{CE} = 5\text{V}$, $I_C = 1\text{A}$	8	—	—	
		$V_{CE} = 5\text{V}$, $I_C = 6\text{A}$	5	—	10	
Fall Time	t_f	$I_C = 6\text{A}$, $I_{B1} = 1.2\text{A}$, $I_{B2} = 2.4\text{A}$	—	0.1	0.3	μs

